

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	88	(InGa <sub>N</sub> or AlGa <sub>N</sub> or AlGaIn <sub>N</sub> or Ga <sub>N</sub> or (gallium near nitride) or (Group with III with nitride)) and ((oxygen or "O.sub.2") with ((flow\$3 near4 rate) or sccm)) and ((oxygen or "O.sub.2") with (dop \$3 or impurity))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 08:51
L2	49	1 and (@ad or @rlad) < "20031202"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 08:54
L3	16	(InGa <sub>N</sub> or AlGa <sub>N</sub> or AlGaIn <sub>N</sub> or Ga <sub>N</sub> or (gallium near nitride) or (Group with III with nitride)) and ((oxygen or "O.sub.2") with doping with efficiency) and ((oxygen or "O.sub.2") with (dop\$3 or impurity))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 09:26
L4	50	(InGa <sub>N</sub> or AlGa <sub>N</sub> or AlGaIn <sub>N</sub> or Ga <sub>N</sub> or (gallium near nitride) or (Group with III with nitride)) and ((oxygen or "O.sub.2") with dop \$3 with ((active near layer) or (emitting near layer))) and ((oxygen or "O.sub.2") with (dop\$3 or impurity))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 09:57
L5	38	4 and (@ad or @rlad) < "20031202"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 09:58

L9	1	09/320459	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 10:07
L10	8	"320459".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 10:07
L12	19	("5821568"   "5909036"   "6072197"   "6086673"   "6107162"   "6225650"   "6335546"   "6411636"   "6542526"   "6576533").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 10:15
L13	7	"098051".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 10:16
L14	7	"098501".ap.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 10:17
L15	234	(InGa <sub>N</sub> or AlGa <sub>N</sub> or AlGa <sub>1-n</sub> N or Ga <sub>N</sub> or (gallium near nitride) or (Group with III with nitride)) and ((oxygen or "O.sub.2" or sulfur or S or selenium or Se) with dop\$3 with ((active near layer) or (emitting near layer)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 10:27

L16	268	(InGa <sub>N</sub> or AlGa <sub>N</sub> or AlGaIn <sub>N</sub> or Ga <sub>N</sub> or (gallium near nitride) or (Group with III with nitride)) and ((oxygen or "O.sub.2" or sulfur or S or selenium or Se) with dop\$3 with ((active near layer) or (emitting near layer) or (quantum near2 well)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 10:28
L17	204	16 and (@ad or @rlad) < "20031202"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 10:29
L18	1000	257/14.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 10:30
L19	13	17 and ((oxygen or sulfur or selenium) with (dop\$3 or impurity)).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 10:33
S5	369	(Ga <sub>N</sub> or (gallium near nitride) or (Group near III) or (nitride near2 semiconductor)) and ((dop\$3 or impurity or acceptor or donor) with (oxygen sulfur or selenium or tellurium)) and (well with barrier) and (quantum near2 well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/21 23:24

S6	289	(GaN or (gallium near nitride) or (Group near III near nitride) or (nitride near2 semiconductor)) and ((dop\$3 or impurity or acceptor or donor) with (oxygen sulfur or selenium or tellurium)) and (well with barrier) and (quantum near2 well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/21 23:24
S7	309	S5 and (MOCVD or CVD or (vapor near2 deposition))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/21 23:28
S8	245	S7 and (@ad or @rlad) < "20031202"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/21 23:28
S9	72	S8 and (flow near2 rate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/21 23:30
S12	93	S8 and ((oxygen or sulfur) same nitrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/21 23:50
S13	81	(GaN or (gallium near nitride) or (Group near III) or (nitride near2 semiconductor)) and ((dop\$3 or impurity) with (oxygen or "O.sub.2")) and ((oxygen or "O.sub.2") with increas\$3 with (flow or rate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 00:03

S14	60	S13 and (@ad or @rlad) < "20031202"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 00:04
S15	137	(GaN or (gallium near nitride) or (Group with III with nitride)) and ((dop\$3 or impurity) with (oxygen or "O.sub.2")) and ((oxygen or "O.sub.2") with ("mmol/min" or "mol/min" or ppm or sccm))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 00:01
S16	94	S15 and (@ad or @rlad) < "20031202"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 00:03
S18	68	S16 and ((ammonia or "NH.sub.3" or "N.sub.2") with (oxygen or "O.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 00:24
S19	46	S18 and (TMG or TMI or TMA or pre \$1cursor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 00:25
S20	546	(GaN or (gallium near nitride) or (Group with III with nitride)) and ((TMG or Ga) with (sccm or rate)) and ((oxygen or "O.sub.2") with (rate or sccm))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 00:50
S21	9	S20 and (oxygen with dop\$3 with efficiency)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 00:51

S22	5	(GaN or (gallium near nitride) or (Group with III with nitride)) and (TMG with (sccm or rate)) and ((oxygen or "O.sub.2") with (rate or sccm)) and (oxygen with (dop\$3 or impurity))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 00:58
S23	39	(GaN or (gallium near nitride) or (Group with III with nitride)) and ((TMG or Ga) with (sccm or (flow\$3 near4 rate))) and ((oxygen or "O.sub.2") with ((flow\$3 near4 rate) or sccm)) and (oxygen with (dop\$3 or impurity))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 01:06
S24	19	S23 and (@ad or @rlad) < "20031202"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 01:07
S27	6	(InGaN or AlGaN or AlGaInN or GaN or (gallium near nitride) or (Group with III with nitride)) and ((TMG or TMI or TMA) with (sccm or (flow\$3 near4 rate))) and ((oxygen or "O.sub.2") with ((flow\$3 near4 rate) or sccm))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/02/04 01:14

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